Radiation Tolerance of Oxygenated n-strip Read-out Silicon Detectors

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Introduction



- Radiation damage to silicon detectors increases reverse currents, creates interface trapped charge, introduces traps, reducing charge collection efficiencies changes the effective doping concentrations
- Studies of the effective doping changes have shown reduced susceptibility to charged hadron irradiation when high concentrations of interstitial oxygen are introduced (RD48)
- However, the other effects, in particular the trapping, do not seem to show corresponding improvements in radiation tolerance

Introduction



• Effective doping concentration, N_{eff} , for a diode of thickness, w, is derived from the voltage needed to fully deplete the diode, V_{fd} (>> V_{bi}), through the equation:

$$V_{\rm fd} = \frac{1}{2} e w^2 N_{\rm eff} / \varepsilon_{\rm Si}$$

- Since C ∝ 1/w, V ∝ 1/C² for V << V_{fd} allowing N_{eff} to be extracted from C(V)
- Because of the effects of trapping, the charge collection efficiency (CCE) as a function of voltage does not saturate at V_{fd} and for segmented detectors read out from the p-side, CCE(V) continues to rise, well above V_{fd}

Evaluation of Trapping Effects



Corresponding Charge Collection Efficiency vs Voltage



Normalised (to Q_M) charge collection for (a) non-irradiated and (b) oxygenenriched detector after 5.1·10¹⁴ p cm⁻²

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Evaluation of Trapping Effects



- The effects of trapping can be parameterised in terms of effective trapping time (*Kramberger et al.*) or, equivalently, velocity dependent attenuation length (*Marti i Garcia et al.*)
- In both cases, trapping is highest where the field is lowest
- These parameterisations assume timescales such that the total untrapped charge is collected, integrating over transient effects.
- Both analyses give values of β (averaged over *e* and *h*) that agree. $\beta_{e,h} \times \Phi_{eq} = 1/\tau_{eff e,h}$ (trapping \propto flux)

($\beta_{e,h}$ ~ 5 ×10⁻¹⁶ cm²/ns)



Annealing of Irradiated Detectors

- Oxygenated and nonoxygenated detectors with both p-side and n-side read-out have been studied
- These have been irradiated in the CERN-PS and annealed to the minimum of the N_{eff} vs time annealing curve



- We have previously reported excellent fits to the CCE(V) for irradiated detectors based on the parameterisation of Marti i Garcia et al using attenuation^g length ∝ v_{drift} up to v_{saturation}
- Free parameters:
 - attenuation length λ , depletion voltage V_{FD} total generated charge Q₀



1.9×10¹⁴ p/cm²







 $2.9 \times 10^{14} \, p/cm^2$

5.1×10¹⁴ p/cm²

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Detector label	Fluence [p cm ⁻²]	Oxygen enrichment	V _{FD} [V] (From C-V)	V _{FD} [V] (From CCE)	λ [μm]
NI	Non irr.	No	49 ± 2	50 ± 2	
SO1	1.9±0.1 · 10 ¹⁴	Yes	100 ± 7	90 ± 2	1338 ± 15
SN1	1.9±0.1 · 10 ¹⁴	No	150 ± 8	137 ± 2	1407 ± 220
502	2.9±0.2 · 10 ¹⁴	Yes	121 ± 7	130 ± 2	1224 ± 138
SN2	2.9±0.2 · 10 ¹⁴	No	218 ± 15	214 ± 4	1313 ± 122
SO3	5.1 ±0.4 · 10 ¹⁴	Yes	181 ± 15	196 ± 3	731 ± 84
SN3	5.1±0.4 · 10 ¹⁴	No	320 ± 20	348 ± 7	781 ± 55



- The fitted values of V_{FD} agree with each other and with oxygenated data from RD48 (CERN LHCC 2000-009) taking account of the proton damage factor
- The fitted values of Q₀: 18.1±0.3, 18.2±0.3, 17.7±0.3, 18.1±0.6, 18.2±0.4 and 18.3±0.4 are all consistent and agree with the preirradiation value 17.9±0.3



ADC/300micron

 Because high resistivity n-type bulk detectors become effectively ptype after heavy hadron irradiation, read-out using segmentation of the n-implants allows charge to be collected on the high field side, giving higher CCE at lower V.

Comparison of p-type and n-type detectors using ¹⁰⁶Ru β-source after 3×10¹⁴ p/cm² (SCT-128A read-out)







Detectors for the LHC-b Experiment

- The LHC-b vertex locator VeLo uses oxygenated 200µm thick detectors.
- Prototypes have been fabricated using both p-strip and n-strip readout and irradiated at the CERN PS.



Detectors for the LHC-b Experiment



Detectors for the LHC-b Experiment



 Super-LHC is proposed with a factor of 10 increased luminosity.





Detectors Studied



- Studies have been carried out with full-sized LHC-b prototypes using SCT-128 analogue readout and miniature (cm×cm) micro-strip detectors using SCT-128 or wide bandwidth (Phillips 6954) current amplifier.
- CCE(V) has been studied using a ¹⁰⁶Ru β-source and a 1064nm light spot (where the latter is tuned to give an energy deposit about 3 times that of a minimum ionising particle)
- All give comparable results.





Bias (volts)

CCE(*V*) for irradiated, 200 μ m thick, LHC-b n-in-n full-size prototype detector with laser data (normalised to value at 400V) superimposed



LHC-b Prototype CCE(V) Results

- From fits to the CCE(V), the depletion voltages for the different regions of the detector can be extracted.
- These detectors were processed by Micron Semiconductor Ltd to Liverpool designs on oxygenated (> 10¹⁷ cm⁻³) FZ 200μm thick 6" wafers.
- Given the thickness, the depletion voltages agree well with previous proton irradiation measurements, corroborating the dose estimates.



200

CCE(*V*) extracted depletion voltages vs strip number for non-uniformly irradiated n-strip LHC-b 'φ-detector'



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LHC-b Prototype CCE(V) Results

- The CCE(V) values at high voltage for n-side read-out with respect to the non-irradiated value show limited signal loss even after 7.10¹⁴p/cm².
- The tracking parts of ATLAS and CMS are designed for an integrated dose after 10 years equivalent to 3.10¹⁴p/cm² although their pixel vertex detectors and the LHC-b VeLo have to survive much more.
- Should Super-LHC go ahead, the ATLAS and CMS trackers will need to be affordably upgraded 1st RD50 Workshop, 2-4 Oct. 2002



 $^{106}\text{Ru}\ \beta\text{-source}\ \text{CCE}$ at high voltage vs dose for the LHC-b n-in-n prototype



n-side vs p-side read-out

- For simple one dimensional structures eg large area diodes little difference is expected between the signals seen on the n-side or the p-side.
- However, for segmented detectors as designed for experiments, the key issue is the operating voltage for a given CCE after heavy irradiation.
- Direct comparisons of n-side and p-side detectors with the same masks fabricated on the same material confirm the superiority of n-side read-out after irradiation.

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1060nm laser CCE(*V*) for the highest dose regions of an n-in-n (7.10¹⁴p/cm²) and p-in-n (6.10¹⁴p/cm²) irradiated LHC-b full-size prototype detector.



Conclusions

- Operationally, for position resolution and tracking efficiency the key parameter is the signal/noise.
- After irradiation, at the LHC, although other effects may raise the noise, the key deterioration <u>as a position sensitive</u> <u>detector</u> is in terms of the collected charge.
- The charge collected at a given voltage is reduced <u>both</u> by the trapping <u>and</u> by the changes to the effective doping concentration.
- The former is addressed by n-side read-out while the latter can be helped by using an oxygen enhanced substrate.
- Combining the techniques of n-side read-out (to reduce the influence of trapping) and enhanced interstitial oxygen should yield tracking detectors good to 10¹⁵p/cm² at least.